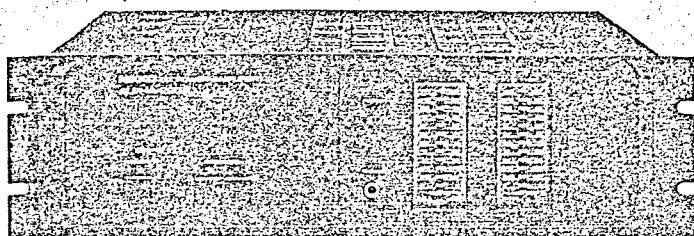


NIKKO**POWER AMP****ALPHA 220**
STEREO POWER AMPLIFIER**TYPE AND VOLTAGE**

W-TYPE: UL and CSA type	120V AC
E -TYPE: NK-STD type	220V AC
B -TYPE: BS type	240V AC

SERVICE MANUAL**CONTENTS**

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SPECIFICATIONS

AMPLIFIER SECTION

Continuous Power Output per Channel:

20 ~ 20000 Hz (8 ohms)	more than 120 Watts
20 ~ 20000 Hz (4 ohms)	more than 130 Watts
1000 Hz (8 ohms)	more than 120 Watts
1000 Hz (4 ohms)	more than 130 Watts

T. H. Distortion, 8 ohms:

at Continuous Power Output . . .	no more than 0.008%
at 1 Watt Power Output	no more than 0.02%

T. H. Distortion, 4 ohms:

at Continuous Power Output . . .	no more than 0.02%
----------------------------------	--------------------

I. M. Distortion, 8 ohms:

at Continuous Power Output . . .	no more than 0.01%
at 1 Watt Power Output	no more than 0.02%

IHF Power Bandwidth, 8 ohms: 5 ~ 70000Hz

Damping Factor at 1000 Hz, 8 ohms: more than 60

Frequency Response, "NORMAL" input, 8 ohms:

at 1 Watt power Output . . . 10 ~ 100000Hz +0, -1dB

Input Sensitivity for 120 Watts Power Output:

MAIN IN 1V ± 2dB

Signal to Noise Ratio, IHF "A" Network:

MAIN (NORMAL, DIRECT) . . . better than 105dB

Signal to Noise Ratio, DIN Filter:

MAIN IN (NORMAL, DIRECT) . . . better than 90dB

Channel Balance: no more than 1dB

Residual Hum and Noise, 8 ohms: . . . no more than 0.5mV

Idling Current: 40 ~ 120mA

Midpoint Voltage: 0 ± 20mV

Muting Delay Time: 3 ~ 7 seconds

GENERAL

Power Requirement:

W-TYPE	AC 120V, 60Hz
E-TYPE	AC 220V, 50Hz
B-TYPE	AC 240V, 50Hz

Power Consumption: 480 W (620 VA)

Ambient Temperature during Operation: . . . -10 ~ 30°C

Dimensions:

Width 482 mm (19 inches)

Height 138 mm (5 1/3 inches)

Depth 344 mm (13 1/2 inches)

Weight, without package: 13.5 kg (29.7 lbs)

* Specifications are subject to change without notice.

BLOCK DIAGRAM

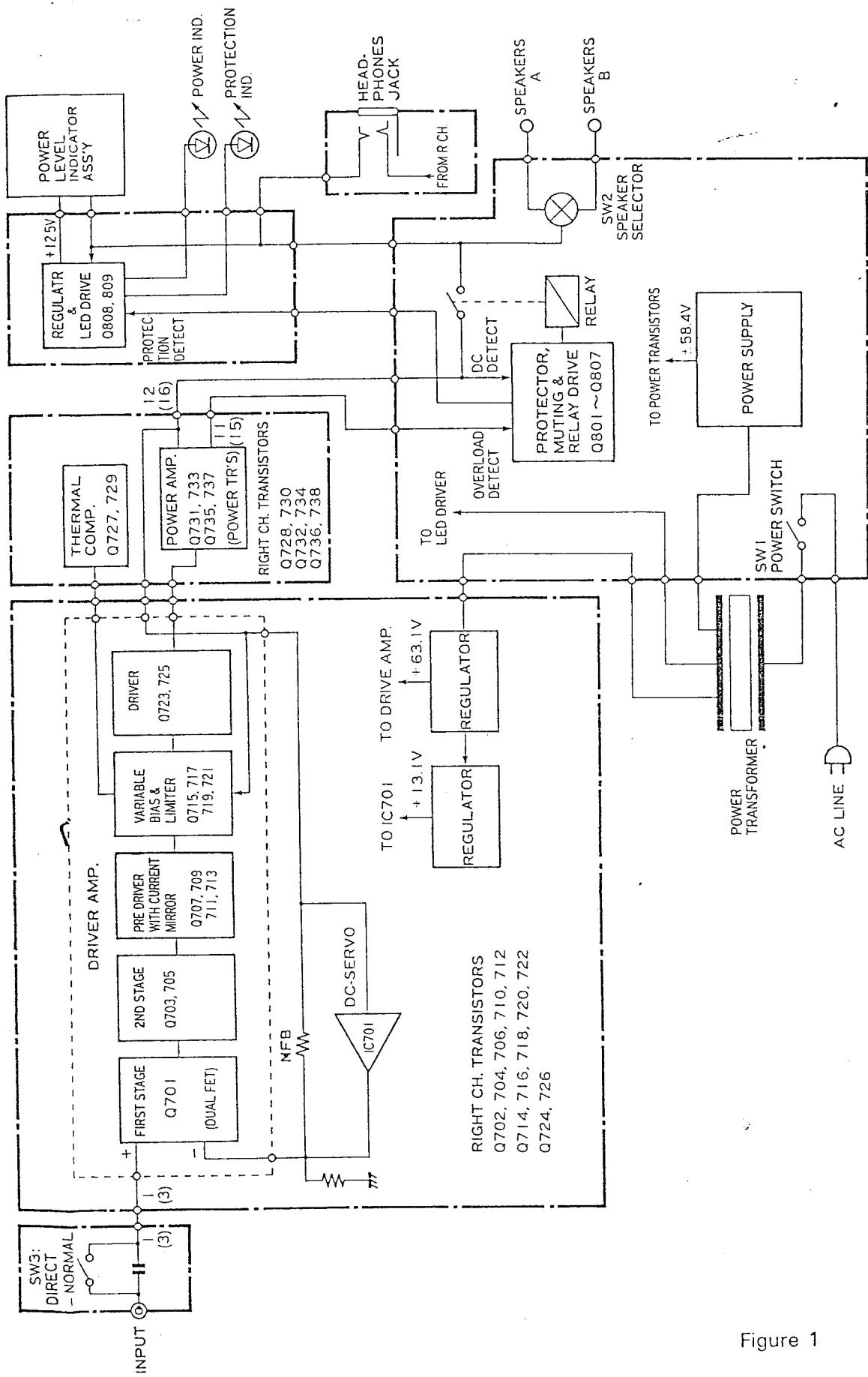


Figure 1

DISASSEMBLY

CABINET COVER REMOVAL

- Remove four tapping screws from the top of the unit.
- Remove four screws from both sides of the unit.
- Lift the cabinet cover away from the unit.

BOTTOM PLATE REMOVAL

- Remove nine tapping screws from the bottom of the unit as shown in Photo 1. (#1 – #9)
- Lift the bottom plate away from the unit.

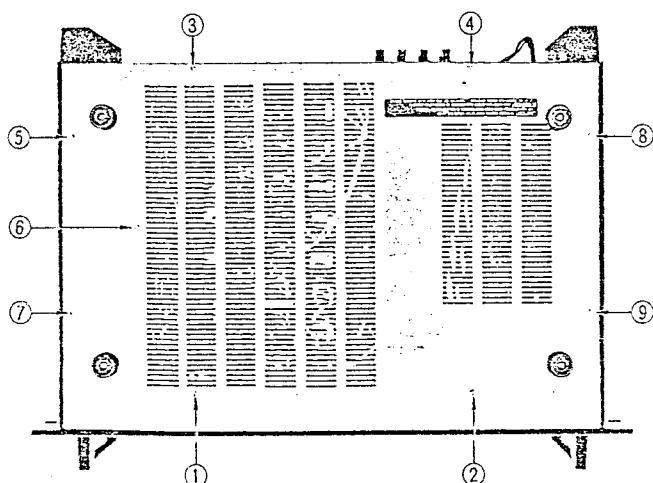


Photo 1

FRONT PANEL REMOVAL

- Remove three tapping screws (#1 – #3) from the left side of the unit as shown in Photo 2.
- Similarly remove three tapping screws from the right side of the unit.
- Remove the front panel away from the unit by pulling it forward.

POWER TRANSFORMER REMOVAL

- Remove the cabinet cover and the bottom plate.
- Disconnect all the cables from the power transformer.
- Remove four nuts (#1 – #4) from the chassis as shown in Photo 3.
- Lift the power transformer away from the unit.

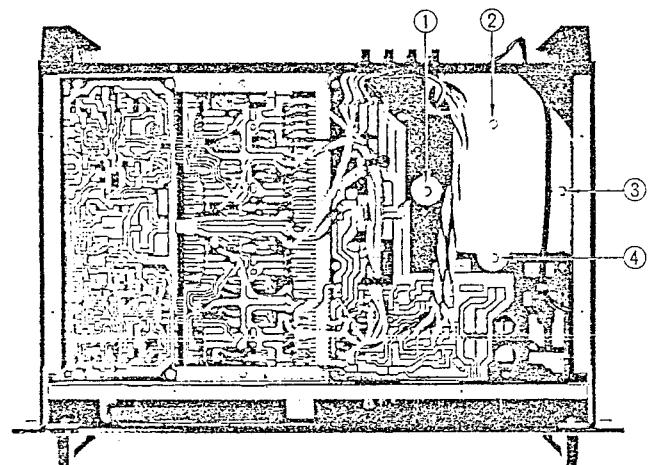


Photo 3

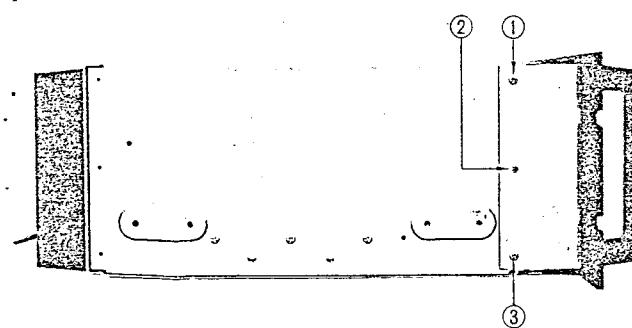


Photo 2

CIRCUIT DESCRIPTION

IIKKO's ALPHA 220, adopting latest devices such as Si-FET power transistors, is of a design introducing a variable bias circuit (non-switching circuit), a DC servo circuit and other most advanced techniques.

For details, refer to page 2 "BLOCK DIAGRAM" and page 8 "SCHEMATIC DIAGRAM".

The following are explanations of the main circuits and devices.

VARIABLE BIAS CIRCUIT

Currently, in the output stage of power amplifiers are mostly used SEPP (Single Ended Push Pull) circuits. (Fig. 2).

It is generally known that the current (idle current) flowing through NPN and PNP transistors of this circuit can be classified into three large groups of operation form, class "A", class "AB" and class "B". (Fig. 3).

In class "A" operation, neither of collector currents, Q_1 and Q_2 , becomes zero nor cut off. Even when the current flowing to the load R_L is zero, a certain current is flowing through Q_1 and Q_2 , and so no crossover distortion exists theoretically.

To realize perfect class "A" operation, however, a current equal to or more than maximum output should continue to be let flow at the output stage as idle current, causing class "A" operation to prove to

be a poor efficiency system.

In class "AB" or "B" operation, the Q_1 plays the role of amplification of the plus part of the signal and Q_2 that of the minus part, no matter whether idle current is large or small.

In other words, there definitely exists a period in which, when one transistor is on, the other transistor keeps cutting off, in these operations.

Switching distortion or crossover distortion is caused at the moment of this active status turning into cut-off status or the cut-off status into the active status. Nevertheless, as these operation forms have high efficiency with small idle current, it is much easier to use class "AB" or "B" operation for high power amplification rather than class "A".

A power amplifier enjoying the merit of each of these systems — that is, practically no crossover or switching distortion being caused in class "A" operation and easier high power amplification being achieved by class "B" — has been realized by adopting the variable bias circuit.

The idea of a variable bias circuit is that in no case the output stage is allowed to be cut-off by increasing and decreasing bias voltage in corresponding with the voltage of input signal.

Fig. 4 shows the variable bias circuit adopted in ALPHA 220.

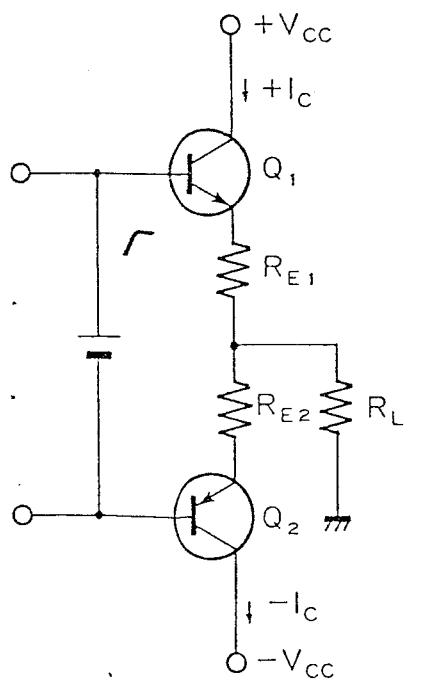


Figure 2 SEEP CIRCUIT

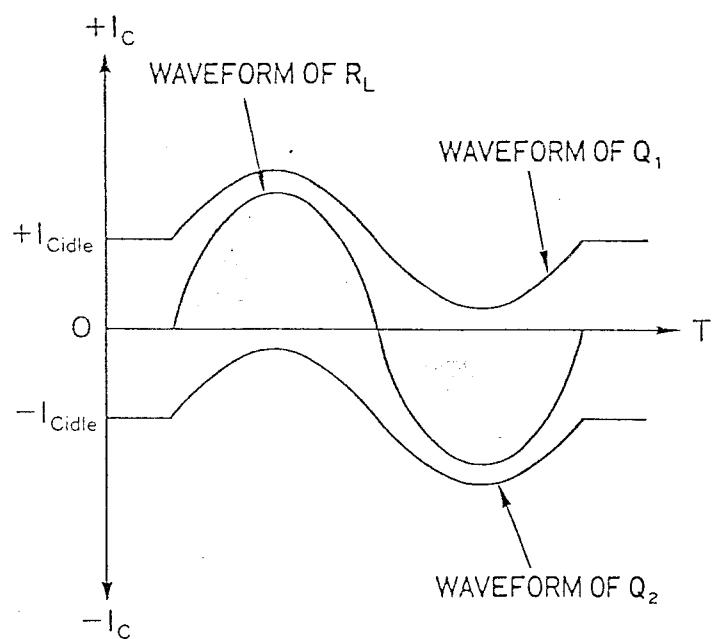


Figure 3-1 CLASS-A OPERATION

3. Hi-fT POWER TRANSISTORS

For details characteristics, refer to "SEMICONDUCTOR DATA" at the end of this manual.

The power transistors employed in ALPHA 220 realize an f_T (Current Gain-bandwidth Product) of 80 MHz with NPN type and 60 MHz with PNP type (each being a typical value) in spite of its high P_c (Collector Power Dissipation) such as 150 W (The value when $T_c = 25^\circ\text{C}$). Compared with conventional transistors with a P_c of 150 W where f_T was around 10 MHz at maximum, the high speed attained by these Hi-fT power transistors is remarkable.

Such high f_T has been realized specially by the inside construction of these transistors which is greatly different from that of conventional ones — the multi-emitter construction.

In this construction, the emitter inside the transistor is divided into many units and emitter resistors with small resistance are inserted to each unit, resulting in a parallel connection.

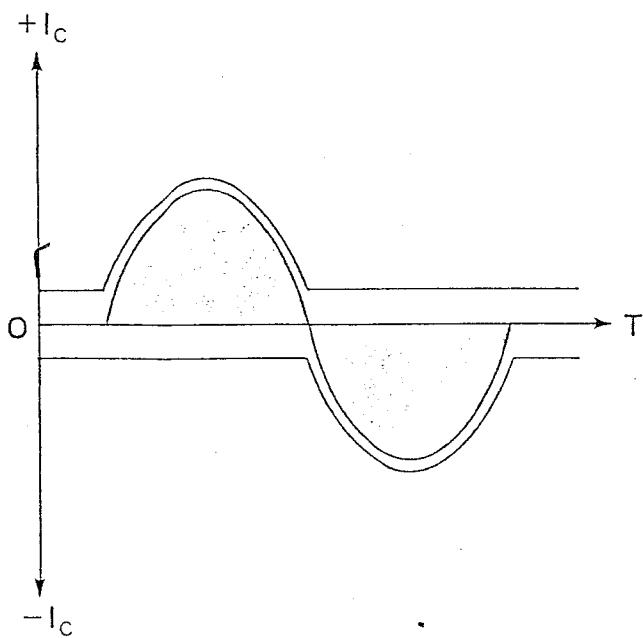


Figure 3-4 OPERATION OF VARIABLE BIAS

This equivalently means that many small signal transistors with high f_T and switching speed are parallelly connected, which has made it possible to realize such a high power characteristic while maintaining high switching speed.

Thanks to such construction as mentioned above, these power transistors are excellent in linearity of its h_{fe} .

Furthermore, as dissipation is dispersed equally to each emitter due to the emitter-divided construction, they have another feature of being strong against breakdown as compared with conventional power transistors.

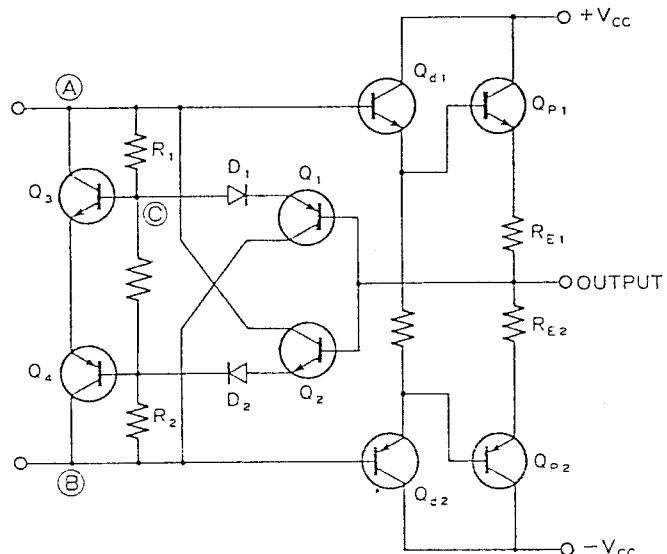


Figure 4 VARIABLE-BIAS CIRCUIT

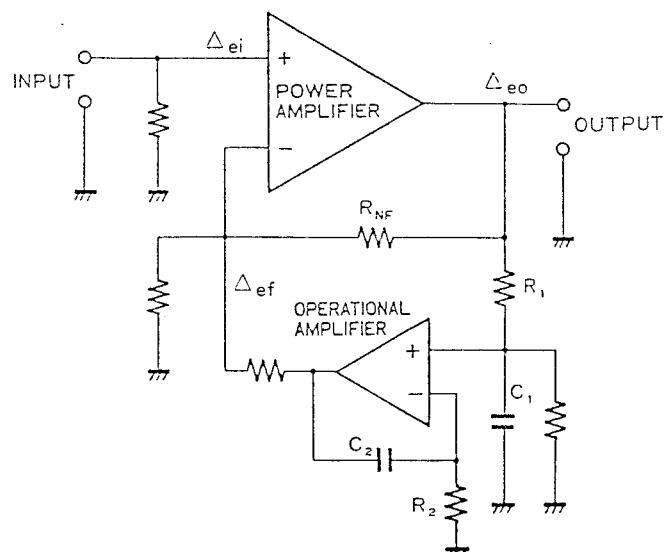


Figure 5 DC-SERVO CIRCUIT

PARTS LOCATION

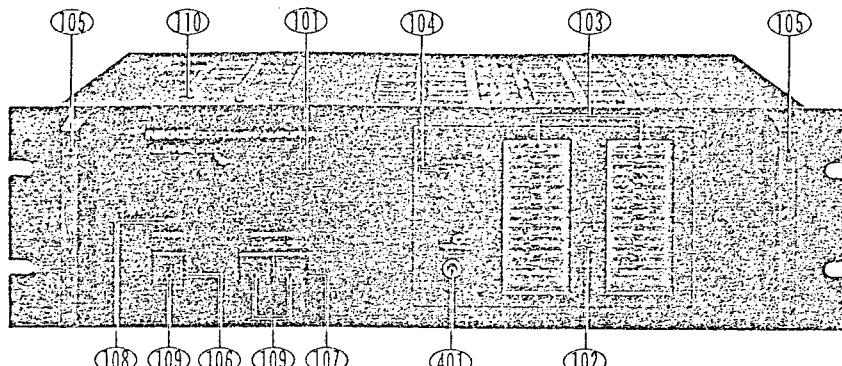


Photo 4

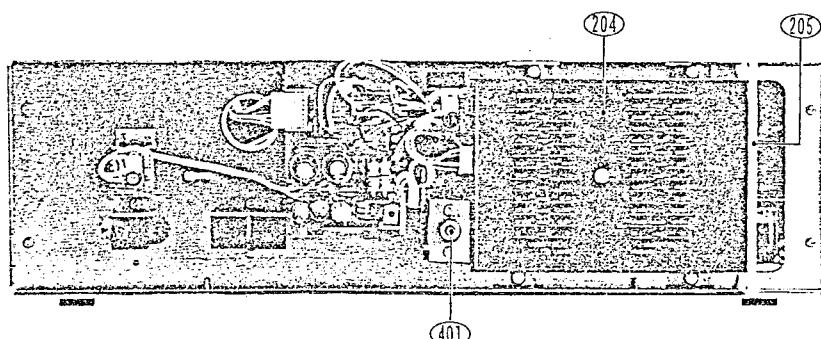


Photo 5

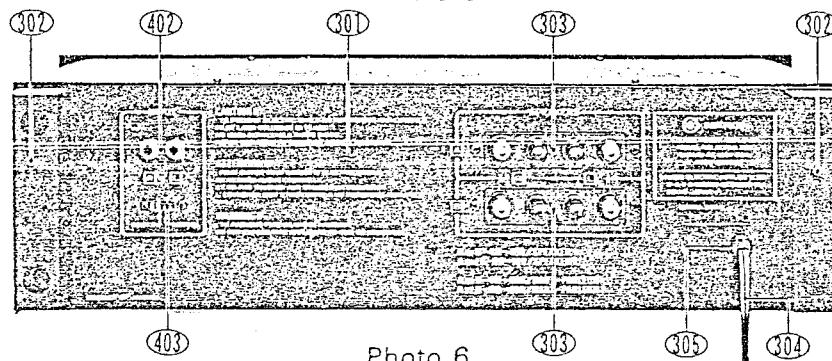


Photo 6

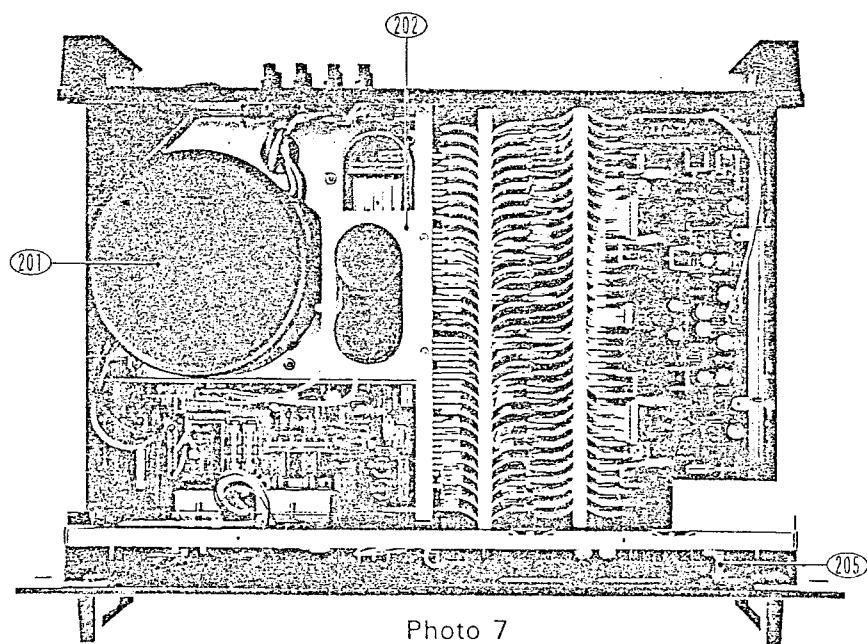


Photo 7

ALIGNMENT

ALIGNMENT PRECAUTIONS

1. As the ALPHA 220 is a power amplifier with large output power, it consumes much electrical power and a great amount of current flows in the power source line of the primary side. Therefore, in the case when it is connected to the source by an extension cord, the size of the extension cord should be equal or larger than that of the power source cord of the ALPHA 220. Otherwise, the voltage might be reduced or the extension cord might generate excessive heat because of the resistance which the cord has, then not only can proper alignment be done, but also it is very dangerous.

2. If the power sources are supplied to the ALPHA 220 and the instruments by branching off from one cord, the voltage is sometimes dropped down and the stability of the instruments goes down.
The ALPHA 220 and the instruments should be connected to the power sources by using independent cords. The ALPHA 220 must take the power source from AC outlet of the wall side.

3. As there are many parts which hold high voltages in the circuit and the parts inside of the ALPHA 220, be careful not to receive an electric shock. In the case of connecting and taking off the instruments, you must turn off the power switch of the ALPHA 220 before getting on the work.

4. When the circuit happens to be shorted by the drivers or test probes used for alignment through mistake, the circuit and the parts will be damaged. As the damage is larger than that of ordinary amplifiers and receivers, close attention is needed. It is advised that the turning driver, excluding the top part, should be wrapped with insulation tape or a driver made of plastic or some kind of insulating material should be used.

5. As the dummy load resistor generates heat while alignment, it gets very hot and you may be burnt if you touch it with bare hands. It is better if you can put the dummy load resistor in a place away from being touched, but the wire between the dummy load resistor and the amplifier should not be long. Conceive some method, like putting the dummy load resistor in a well ventilated box. Further, as more than 5 A current might flow in the wire connecting the dummy load resistor and the amplifier, at least larger than AWG #18 thick wire should be used.

6. All the adjustments in the following should be done after the slide switch on the rear panel is set in the "NORMAL" position.

TEST EQUIPMENT

Allow a minimum of 10 minutes warm-up for test equipment.

Maintain rated line voltage.

Audio Frequency Generator
Distortion Meter
Oscilloscope
AC Voltmeter
DC Voltmeter
2-Dummy Load Resistors, 8 ohms, 250 W

All the semi fixed resistors of the MAIN AMP PCB are set around the center position temporarily. (HVR701 and HVR702.)

IDLING CURRENT ADJUSTMENT

1. Connect the 8 ohms dummy load resistors to the left and right channel speaker terminals.
2. Connect the DC voltmeter across the wiring terminal No. 12 and "TP-L" (left channel) or No. 16 and "TP-R" (right channel). (see Photo 8)
3. Turning on the power switch of the ALPHA 220. Adjust the semi fixed resistor HVR701 (left channel) or HVR702 (right channel) so that the DC voltmeter indicates $18 \text{ mV} \pm 1 \text{ mV}$.
4. Turn off the power switch of the ALPHA 220 and remove the DC voltmeter.

METER CIRCUIT ADJUSTMENT

NOTE: See illustration, Figure 8, for test equipment hook-up.

1. Connect 8 ohms dummy load resistors to the left and right channel speaker terminals.
2. Connect the AC voltmeter, distortion meter and the oscilloscope to the left (right) channel speaker terminals. Connect the generator to left (right) channel input terminal.
3. Turning on the power switch of the ALPHA 220.
4. Set the frequency of the generator to 1 KHz. Adjust the output level of the generator so as to make the output power 98 W. (28 V AC voltmeter reading.)
5. Adjust the semi-fixed resistors of the POWER LEVEL INDICATOR PCB, so that the LED of "120 W" dimly lights up.
6. Turning off the power switch of the ALPHA 220.
7. Remove all test equipment.

ALPHA 220

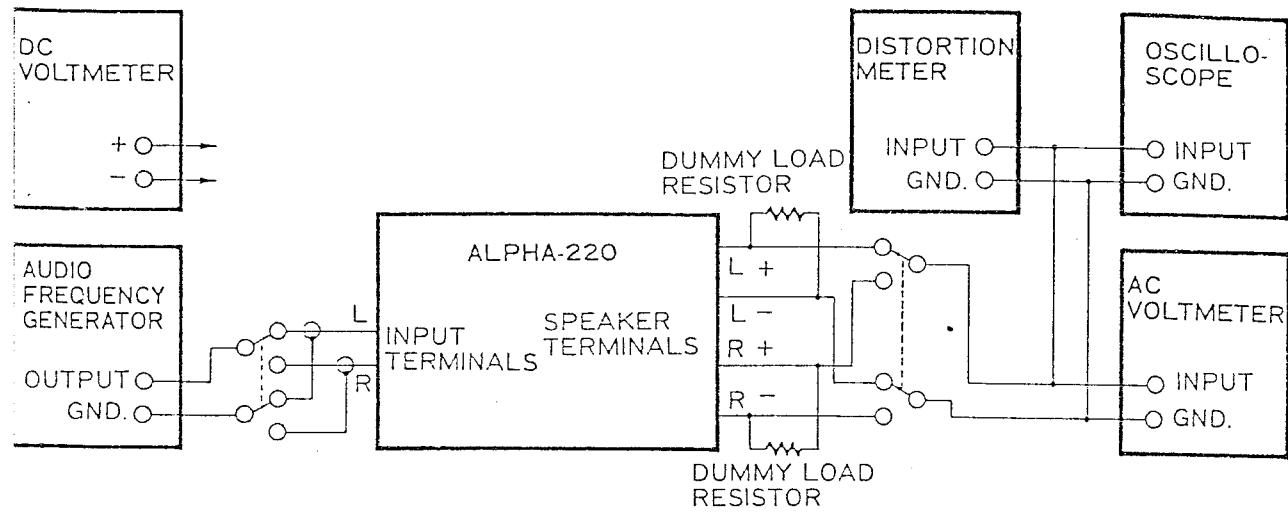


Figure 8 TEST EQUIPMENT HOOK-UP

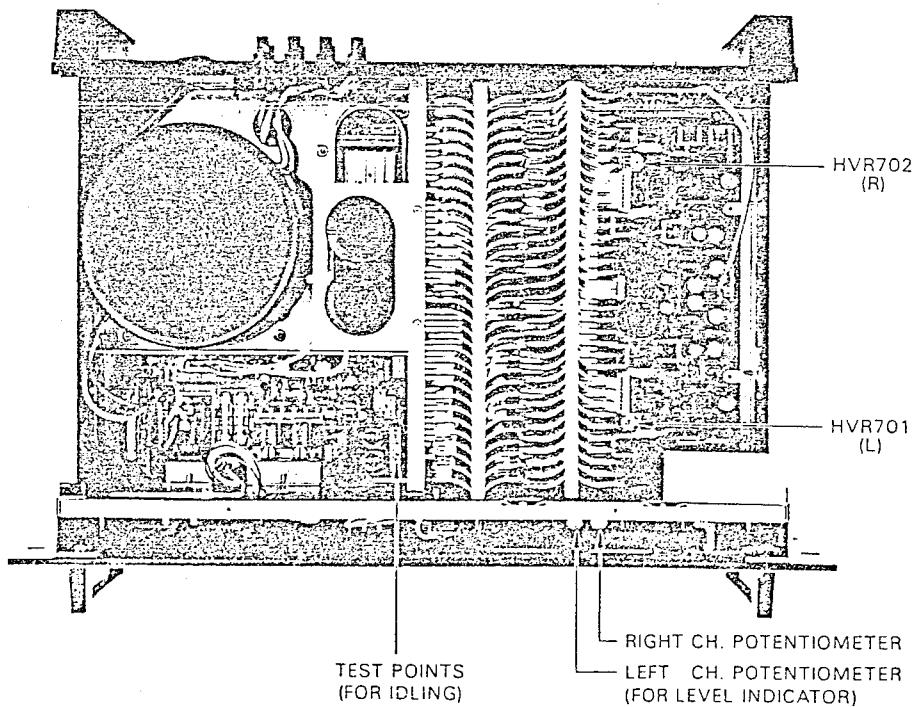


Photo 8 ADJUSTMENT POINTS

PARTS LIST

1. * The KEY NUMBER (#) marked with a (*) on parts list relate to number of three digits with a (). (Photo 4 ~ 7)
2. + Numerals in file indicate the quantity of parts used in one type.
3. ++ TR : Transistor
FET : Field effect transistor
VR : Volume control (Variable resistor)
RES : Carbon film fixed resistor
MO-RES : Metal oxide film fixed resistor
CEM-RES : Cemented wirewound fixed resistor
FP : Flame proof
C-CAP : Ceramic capacitor
E-CAP : Aluminum electrolytic capacitor
M-CAP : Polyester film capacitor
S-CAP : Polystyrene film capacitor
T-CAP : Tantalum electrolytic capacitor
BP-CAP : Bipolar electrolytic capacitor
LC-CAP : Low current leakage electrolytic capacitor.

4. Assemblies and parts are subject to change without notice.

5. Parts ordering procedure:

- A. DO NOT USE THE "KEY" NUMBER AND "SYMBOL" NUMBER.
(these are control # for the factory only)
- B. Include in any order
 - a. Part number.
 - b. Part description.
 - c. Model number.

(any of the above lacking from an order may delay shipment of that order.)

CAUTION:

The mark, the KEY NO. and the SYMBOL NO. circled with rectangle in the schematic diagram and the shaded area in the parts list designate components which have special characteristics important for safety and should be replaced only with types identical to those in the original circuit or specified in the parts list.

KEY NO.	SYMBOL NO.	TYPE+ WEB	DESCRIPTION++ DESCRIPTION++	PART NO.
PACKING MATERIALS & ACCESSORIES				
001	1 1 1	Carton box		9825790
002	2 2 2	Pad		9840970
003	1 1 1	Sack, polyethylen cloth		9640740
004	1 1 1	Sack, polyethylen cloth -- #13		9640320
005a	1 - -	Manual, instructions - English and French		960340E
005b	- 1 1	Manual, instructions - in five different languages		960340K
006	1 - -	Manual, safety instructions		9670410
007a	1 - -	Card, warranty - U.S.A.		967043A
007b	1 - -	Card, warranty - Canada		9670420
008	1 - -	List, service stations		9690210
009	1 1 1	Cord, RCA phono pin plug - 2T-1		962014A
CABINET ASSEMBLY				
*101a	1 1 1	Panel, front - SILVER		7885060
*101b	1 1 1	Panel, front - BLACK		7925050
*102a	1 1 1	Panel, power level indicator - SILVER		7870540
*102b	1 1 1	Panel, power level indicator - BLACK		7870490
*103	1 1 1	Window, power level indicator		7802550
*104	1 1 1	Globe, LED - protection indicator		7402540
*105a	2 2 2	Handle - 100G - SILVER		7490180
*105b	2 2 2	Handle - 100S - BLACK		7490190
*106	1 1 1	Guide, button - 1P18 - power switch		7402550
*107	1 1 1	Guide, button - 2P18 - speakers selector		7402560
*108	1 1 1	Globe, LED - input power indicator		7402120
*109a	3 3 3	Button, push - M18GL - power/speakers, SILVER		7852290
*109b	3 3 3	Button, push - M18SK - power/speakers, BLACK		7852300
*110	1 1 1	Cover, top		7821110
111	1 1 1	Plate, bottom		7326430
112	4 4 4	Foot, polyethylen -- 22φx10		7401350
CHASSIS ASSEMBLY				
*201a	1 - -	Transformer, power - T-1-397 - AC 120V		1103970
*201b	- 1 1	Transformer, power - T-1-413 - AC220 or 240V		1104130
*202	1 1 1	Supporter, filter capacitors		7002510
203	1 1 1	Power level indicator assembly		4582770
*204	1 1 1	Inside panel, power level indicator		7802660
*205	1 1 1	Light guide, level indicator		7401580
206	1 1 1	Lamp - 8V 0.3A		5808210
BACK PLATE ASSEMBLY				
*301a	1 - -	Plate, back - (W)		7326390
*301b	- 1 1	Plate, back - (E)		7326400
*302	2 2 2	Block, terminal guard		7401860
*303	2 2 2	Terminal, speakers - screw type 4P		4450480

KEY NO.	SYMBOL NO.	TYPE+ WEB	DESCRIPTION++ DESCRIPTION++	PART NO.
*304a		1 - -	Cord, AC line - SPT-1	606010A
*304b		- 1 -	Cord, AC line - CEE-2T	600508A
*304c		- - 1	Cord, AC line - BS	600515A
*305a		1 - -	Bush, power cord - SR-3P-4	7400620
*305b		- 1 1	Bush, power cord - SR-4N-4	7400690
MAIN AMP PC BOARD ASSEMBLY				
(POWER OUTPUT SECTION)				
Q727,728	2 2 2	TR 2SD882 (P or Q)		5 13119S
Q729,730	2 2 2	TR 2SB772 (P or Q)		5 11120S
Q731,732,				
Q735,736	4 4 4	TR 2SC2565 (O or R)		5 12127S
Q733,734,				
Q737,738	4 4 4	TR 2SA1095 (O or R)		5 10123S
C741,742	2 2 2	M-CAP 0.047uf 10% 400V		2 73473K
C743				
~ C746	4 4 4	E-CAP 1uf 100V		2 118100
R781				
~ R788	8 8 8	CEM-RES 0.1ohm 2Wx2		3 82109P
R789,790	2 2 2	FP-MO-RES 10ohm 2W		3 62100L
(DRIVER PCB SECTION)				
IC701	1 1 1	IC AN6552		5 18096S
Q701,702	2 2 2	FET 2SK 150A (GR)		5 16038S
Q703				
~ Q706	4 4 4	TR 2SC1845 (E or F)		5 12115S
Q707				
~ Q710	4 4 4	TR 2SA1144 (O or Y)		5 10120S
Q711,712	2 2 2	TR 2SC1941 (L or K)		5 12112S
Q713,714	2 2 2	TR 2SC2704 (O or Y)		5 12122S
Q715,716	2 2 2	TR 2SA992 (E or F)		5 10110S
Q717,718	2 2 2	TR 2SC1845 (E or F)		5 12115S
Q719,720	2 2 2	TR 2SC1815 (Y or GR)		5 12107S
Q721,722	2 2 2	TR 2SA1015 (Y or GR)		5 10102S
Q723,724	2 2 2	TR 2SC2275 (P or Q)		5 12120S
Q725,726	2 2 2	TR 2SA985 (P or Q)		5 10118S
D701				
~ D704	4 4 4	Diode 2-0A90		5 00013G
D705				
~ D708	4 4 4	Diode 1S2076		5 01019S
D709,710	2 2 2	Diode GP10-4002		5 00066S
D802	1 1 1	Diode W02		5 00061S
ZD701				
~ ZD704	4 4 4	Zener diode RD22EB4		5 02059S
ZD705,706	2 2 2	Zener diode RD13EB3		5 02063S
TH701				
~ TH704	4 4 4	Thermistor D2FHL-103S		5 400180

PART ORDERING PROCEDURE ----- DO NOT USE THE "KEY" NUMBER AND "SYMBOL" NUMBER. (these are control # for the factory only.) Include in any order: a. Part number, b. Part description, c. Model number. (any of the above lacking from an order may delay shipment of the order.)

KEY NO.	SYMBOL NO.	TYPE ⁺ WEB	DESCRIPTION ⁺⁺			PART NO.
C703,704	2 2 2	C-CAP 100pf	10%	50V		232101K
C705						
~ C708	4 4 4	E-CAP 100uf	25V			211330Q
C709,710	2 2 2	C-CAP 150pf	10%	50V		232151K
C711,712	2 2 2	M-CAP 0.047uf	10%	200V		272473K
C713,714	2 2 2	C-CAP 6pf	10%	500V		234609K
C715,716	2 2 2	C-CAP 3pf	10%	500V		234309K
C717,718	2 2 2	C-CAP 47pf	10%	500V		234470K
C719,720	2 2 2	C-CAP 100pf	10%	500V		234101K
C721,722	2 2 2	BP-CAP 22uf	16V			215222N
C723,724	2 2 2	BP-CAP 100uf	16V			215230N
C725,726	2 2 2	BP-CAP 22uf	16V			215222N
C727,728	2 2 2	E-CAP 100uf	16V			211230Q
C803,804	2 2 2	E-CAP 1000uf	80V			2100130
HVR701						
~ 702	2 2 2	Potentiometer 5kohm				4301410
R701,702	2 2 2	RES 2.7kohm	5%	%W		328272J
R703,704	2 2 2	RES 47kohm	5%	%W		328473J
R705,706	2 2 2	RES 6.8kohm	5%	%W		328682J
R707						
~ R710	4 4 4	RES 2.7kohm	5%	%W		328272J
R711,712	2 2 2	RES 100ohm	5%	%W		328101J
R713						
~ R716	4 4 4	FP-MO-RES 5.6kohm	5%	1W		361562L
R717,718	2 2 2	RES 560ohm	5%	%W		328561J
R719,720	2 2 2	RES 15kohm	5%	%W		328153J
R721						
~ R724	4 4 4	RES 4.7kohm	5%	%W		328472J
R725,726	2 2 2	RES 2.7kohm	5%	%W		328272J
R727						
~ R730	4 4 4	RES 820ohm	5%	%W		328821J
R731,732	2 2 2	RES 82ohm	5%	%W		328820J
R733,734	2 2 2	RES 100ohm	5%	%W		328101J
R735,736	2 2 2	FP-MO-RES 3.9kohm	5%	1W		361392L
R737						
~ R740	4 4 4	RES 180ohm	5%	%W		328181J
R741,742	2 2 2	RES 1kohm	5%	%W		328102J
R743,744	2 2 2	RES 1.8kohm	5%	%W		328182J
R745,746	2 2 2	RES 1kohm	5%	%W		328102J
R747						
~ R750	4 4 4	FP-RES 220ohm	5%	%W		326221L
R751						
~ R754	4 4 4	FP-RES 820ohm	5%	%W		325821L
R755						
~ R758	4 4 4	FP-RES 390ohm	5%	%W		328391L
R759,760	2 2 2	FP-MO-RES 270ohm	5%	1W		361271L
R761,762	2 2 2	RES 100kohm	5%	%W		328104J
R763						
~ R766	4 4 4	RES 10kohm	5%	%W		328103J
R767,768	2 2 2	FP-MO-RES 5.6kohm	5%	1W		361562L
REGULATOR PC BOARD ASSEMBLY						
(REGULATOR SECTION)						
F801	1 --	Fuse - 8A 250V MGC				4700760
F802,803	2 --	Fuse - 0.8A 250V MGC				4700580
F801	-1 1	Midget fuse - T4.0A 250V				4720400
F802,803	-1 1	Midget fuse - T0.8A 250V				4720320
SW1	1 --	Switch, push - SDZ-1P TV-8 - power				4041500
SW1	-1 1	Switch, push - ESB-90179S - power				4041600
D801	1 1 1	Diode S10V820				560058S
C801,802	2 2 2	E-CAP 15000uf 71V				2100120
C806	1 --	M-CAP 0.01uf 125V				284103M
C806	-1 1	M-CAP 0.01uf 250V				283103M
(PROTECTOR SECTION)						
SW2,3	1 1 1	Switch, twin push - SUF-24 - speakers				4041590
RELAY1	1 1 1	Relay - G2Z-222P - DC24V				1700300

KEY NO.	SYMBOL NO.	TYPE ⁺ WEB	DESCRIPTION ⁺⁺		PART NO.
Q801,802	2 2 2	TR 2SC2229 (Y)			512108S
Q803	1 1 1	TR 2SA992 (E or F)			510110S
Q804	1 1 1	TR 2SC1815 (Y or GR)			512107S
Q805	1 1 1	TR 2SA1015 (Y or GR)			510102S
Q806	1 1 1	TR 2SC2235 (O, Y)			512109S
Q807	1 1 1	TR 2SC2240 (Y or GR)			512102S
D803					
~ D807	5 5 5	Diode 1S2076A			501020S
D808	1 1 1	Diode GP10-4002			560066S
ZD801	1 1 1	Zener diode RD22EB4			502059S
L701,702	2 2 2	Coil, choke - 1uH			1210960
C807,808	2 2 2	BP-CAP 1uf 50V			215510N
C809	1 1 1	E-CAP 1uf 50V			211510Q
C810	1 1 1	BP-CAP 100uf 10V			215130N
C811	1 1 1	E-CAP 47uf 25V			211325Q
C812	1 1 1	E-CAP 10uf 16V			211220Q
C818	1 1 1	E-CAP 1uf 50V			211510Q
R791,792	2 2 2	FP-MO-RES 10ohm	5%	2W	362100L
R801,802	2 2 2	RES 2.2kohm	5%	%W	328222J
R803,804	2 2 2	RES 22kohm	5%	%W	328223J
R805,806	2 2 2	RES 82kohm	5%	%W	328223J
R807	1 1 1	RES 56kohm	5%	%W	328563J
R808	1 1 1	RES 18kohm	5%	%W	328183J
R809	1 1 1	RES 100kohm	5%	%W	328104J
R810,811	2 2 2	RES 68kohm	5%	%W	328683J
R812	1 1 1	RES 4.7kohm	5%	%W	328472J
R813	1 1 1	RES 150kohm	5%	%W	328154J
R814	1 1 1	RES 47ohm	5%	%W	328470J
R815	1 1 1	RES 220kohm	5%	%W	328224J
R816	1 1 1	RES 4.7kohm	5%	%W	328472J
R817	1 1 1	FP-MO-RES 1kohm	5%	1W	361102L
(HEADPHONES PCB SECTION)					
*401	1 1 1	Jack, headphones			4550260
(INPUT PCB SECTION)					
Q808	1 1 1	TR 2SC2275 (P or Q)			512120S
Q809	1 1 1	TR 2SC1815 (Y or GR)			512107S
D809,810	2 2 2	Diode GP10-4002			560066S
ZD802	1 1 1	Zener diode RD13EB3			502063S
C813	1 1 1	E-CAP 47uf 16V			211225Q
C814,815	2 2 2	E-CAP 330uf 25V			211333Q
C816	1 1 1	E-CAP 100uf 25V			211330Q
C817	1 1 1	E-CAP 33uf 25V			211323Q
R793,794	2 2 2	FP-MO-RES 330ohm	5%	2W	362331L
R818	1 1 1	FP-RES 270ohm	5%	%W	329271L
R819	1 1 1	RES 1.5kohm	5%	%W	328152J
R821	1 1 1	RES 220kohm	5%	%W	328224J
R822	1 1 1	FP-RES 270ohm	5%	%W	329271L
(POWER INDICATOR SECTION)					
C701,702	2 2 2	BP-CAP 2.2uf 50V			215512N
(PROTECTION INDICATOR SECTION)					
LED801	1 1 1	LED BR5504S			5060300
LED801	1 1 1	Spacer, LED			7903140
(PROTECTION INDICATOR SECTION)					
LED802	1 1 1	LED PR5527S			5060270
LED802	1 1 1	Spacer, LED			7903110

SEMICONDUCTOR DATA

TRANSISTORS

+ NOTES Ge: Germanium
Si: Silicon A: Alloy
B: Base Df: Drift-field
D: Diffused E: Epitaxial
Dd: Double-diffused G: Grown
P: Planar
J: Junction Pc: Point-contact
Td: Triple-diffused

DEVICE TYPE	APPLICATIONS	STRUCTURE	MAXIMUM RATINGS Absolute-Maximum Values: (TA = 25°C unless otherwise specified)						ELECTRICAL CHARACTERISTICS Typical Values: (TA = 25°C unless otherwise specified)										MANUFACTURER		
			Collector-to-Base Voltage VCB (V)	Emitter-to-Base Voltage VEB (V)	Collector Current IC (mA)	Collector Dissipation PC (mW)	Junction Temperature TJ (°C)	Collector Cutoff Current ICBO (μA)	Static Forward-Current Transfer Ratio NFE	VCE (V)	IC (mA)	VCE(sat) (V)	IC (mA)	IE (mA)	f _{ab} (MHz)	VCE (V)	IE (mA)	IC (mA)	Output Capacitance Cob (pF)		
2SA985 (P, QI)	AF, Power amp.	PNP Si-E	-120	-5	-1.5A	25W (Tc=25°C)	150	-1 max.	-120	100 ~ 320	-5	-300	-2 max.	-1A	-100	180	-5	-200*	29	Complementary to 2SC2725	NEC
2SA992 (E, FI)	AF, Low noise	PNP Si-E	-120	-5	-50	500	125	-0.05 max.	-120	300 ~ 800	-6	-0.1	-0.3 max.	-10	-1	100	-6	1	3 max.	Complementary to 2SC1845	NEC
2SA1015 (Y, GR)	AF, General	PNP Si-E	-50	-5	-150	400	125	-0.1 max.	-50	120 ~ 400	-6	-2	-0.3 max.	-100	-10	80 min.	-10	-1*	7 max.	Complementary to 2SC1815	TOSHIBA
2SA1095 (O, RI)	AF, Power amp.	PNP Si-E	-160	-5	-15A	150W (Tc=25°C)	150	-50 max.	-160	55 ~ 160	-5	-1A	-2 max.	-5A	-500	60	-10	-IA*	350	Complementary to 2SC2565	TOSHIBA
2SA1144 (IO, YI)	AF, Driver	PNP Si-E	-150	-5	-50	10W (Tc=25°C)	150	-0.1 max.	-150	80 ~ 240	-5	-10	1 max.	-10	-1	120	-5	-10*	2.5	Complementary to 2SC2704	TOSHIBA
2SB772 (P, QI)	AF, Power amp.	PNP Si-E	-40	-5	-3A	1W	150	-1 max.	-30	100 ~ 320	-2	-20	-0.5 max.	-2A	-200	80	-5	100	55	Complementary to 2SD882	NEC
2SC1815 (Y, GR)	AF, General	NPN Si-E	60	5	150	400	125	0.1 max.	60	120 ~ 400	6	2	0.25 max.	100	10	80 min.	10	1*	3 max.	Complementary to 2SA1015	TOSHIBA
2SC1845 (E, FI)	AF, Low noise	NPN Si-E	120	5	50	500	125	0.05 max.	120	300 ~ 800	6	0.1	0.3 max.	10	1	110	6	-1	2.5 max.	Complementary to 2SA992	NEC
2SC1941 (IL, XI)	AF, Driver	NPN Si-E	160	5	50	800	150	0.1 max.	160	135 ~ 400	10	1	0.6 max.	20	2	120	10	-10	3 max.		NEC
2SC2229 (O, YI)	AF, Driver	NPN Si-Td	200	5	50	800	150	0.1 max.	200	70 ~ 240	5	10	0.5 max.	10	1	120	30	10*	5 max.		TOSHIBA
2SC2335 (O, YI)	AF, Driver	NPN Si-E	120	5	800	900	150	1 max.	120	80 ~ 240	5	100	1 max.	500	50	120	5	100*	30 max.		TOSHIBA
2SC2340 (IGR, BLI)	AF, Low Noise	NPN Si-E	120	5	100	300	125	0.1 max.	120	200 ~ 700	6	2	0.3 max.	10	1	100	6	1*	3		TOSHIBA
2SC275 (P, QI)	AF, Power amp.	NPN Si-E	120	5	1.5A	25W (Tc=25°C)	150	1 max.	120	100 ~ 320	5	300	2 max.	1A	100	200	5	200*	19	Complementary to 2SA995	NEC
2SC585 (O, RI)	AF, Power amp.	NPN Si-E	160	5	15A	150W (Tc=25°C)	150	50 max.	160	55 ~ 160	5	1A	2 max.	5A	500	80	10	1A*	200	Complementary to 2SA1095	TOSHIBA
2SC704 (O, YI)	AF, Driver	NPN Si-E	150	5	50	10W (Tc=25°C)	150	0.1 max.	150	80 ~ 240	5	10	1 max.	10	1	200	5	10*	1.8	Complementary to 2SA1144	TOSHIBA
2SD882 (P, QI)	AF, Power amp.	NPN Si-E	40	5	3A	1W	150	1 max.	30	100 ~ 320	2	20	0.5 max.	2A	200	90	5	-100	45	Complementary to 2SB772	NEC

FIELD EFFECT TRANSISTOR

DEVICE TYPE	APPLICATIONS	STRUCTURE	MAXIMUM RATINGS Absolute-Maximum Values: (TA = 25°C unless otherwise specified)						ELECTRICAL CHARACTERISTICS Typical Values: (TA = 25°C unless otherwise specified)										MANUFACTURER
			Gate-to-Gate-to-Drain Source Current ID (mA)	Gate-to-Drain Current ID (mA)	Drain Current ID (mA)	Total Drain Dissipation PD (mW)	Channel Temperature Tch (°C)	Gate-Leak Current Test Conditions (nA)	Gate-to-Drain Breakdown Voltage V _{GD} (V)	Drain Current Test Conditions (mA)	Gate-to-Source Cutoff Voltage V _{GSC} (V)	Forward Transfer Admittance Test Conditions (MΩ)	Feed Back Admittance Test Conditions (MΩ)	Power Gain (Common Source) Test Conditions (dB)	Noise Figure Test Conditions (dB)	Test Conditions (dB)	Test Conditions (dB)	Test Conditions (dB)	
2SK150 (A, IGR)	AF, Low noise Differential amp.	Si-N-channel junction (Dual)	-50	-50	10	200	125	V _{GS} = -30V V _{DS} >0	-1 max.	V _{DS} =10V V _{GS} =0	2.6 ~ 8.5		V _{DS} =10V V _{GS} =0 ID=3mA	12	V _{DS} =10V ID=0 f=1kHz	3	V _{DS} =10V ID=1mA f=1kHz	2 max.	TOSHIBA

DIODES, LED'S

DEVICE TYPE	APPLICATIONS	STRUCTURE	MAXIMUM RATINGS Absolute-Maximum Values: (TA = 25°C unless otherwise specified)								ELECTRICAL CHARACTERISTICS Typical Values: (TA = 25°C unless otherwise specified)								MANUFACTURER
			Reverse Surge Voltage VR (V)	Peak Reverse Voltage VRM (V)	Reverse Peak Current IF (mA)	Forward Peak Current IFM (mA)	Average Rectified Current IR (mA)	Forward Surge Current IF surge (mA)	Forward Junction Temperature TJ (°C)	Total Power Dissipation PD (mW)	Forward Current IFmin (mA)	Forward Voltage V _{fm} (V)	Reverse Current IRmax (mA)	Reverse Current VR (V)	Others				
2D490	Detector	Ge-Pc			15		150		0.4	75	4	I							MATSUSHITA
1S2076	Medium speed Switching	Si-EP	35	30		450	150	1	175	250			0.8	10	1	30			HITACHI
1S2076A	Medium speed Switching	Si-EP	70	60		450	150	1	175	250			0.8	10	1	30			HITACHI
GP10-5002	Rectifier	Si-DJ	100	70			1A	30	175				1.1	1A	5				GENERAL INSTRUMENT
W02	Rectifier	Si-DJ (Bridge)		200	200		1.5A	50	125				1.0	1A	10		P _m = 50°C/W		GENERAL INSTRUMENT
S10VB20	Rectifier	Si-DJ (Bridge)		200			10A	200	150				1.05		10				SHINDENGEN
EP5504S	Lamp (red)	GaAlAs			4		300	I _f = 50		85	100		2.0	20	100	4	I _f = 80 mA (I _f = 20 mA)		STANLEY
PR5575	Lamp (red)	GaP			4		100	I _f = 30		85	75		2.0	10	100	4	I _f = 1.2 mA (I _f = 10 mA)		STANLEY

ZENER DIODES

DEVICE TYPE	APPLICATIONS	STRUCTURE	MAXIMUM RATINGS Absolute-Maximum Values: (TA = 25°C unless otherwise specified)						ELECTRICAL CHARACTERISTICS Typical Values: (TA = 25°C unless otherwise specified)										MANUFACTURER	
			Total Power Dissipation PD (mW)	Zener Current I _Z (mA)	Junction Temperature T _J (°C)	Zener Voltage V _Z (V)	Test Conditions	Differential Resistance R _Z (Ω)	Test Conditions	Temperature Coefficient T _Z (ppm/°C)	Test Conditions	Reverse Current I _Z (mA)	Test Conditions	Others						
RD13E83	Regulator	Si-J	400		175	12.99		13.66	10		25	10				2	10			NEC
RD22E84	Regulator	Si-J	400		175	21.52		22.63	5		60	5				2	17			NEC

INTEGRATED CIRCUITS AN6552

Manufacturer: MATSUSHITA

Applications: Dual Operational Amplifier

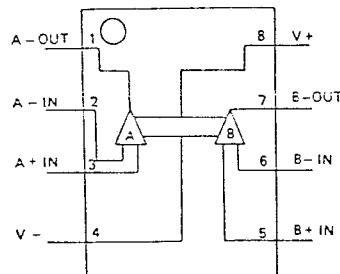
BSOLUTE MAXIMUM RATINGS

Supply Voltage	$\pm 18\text{ V}$	Input Voltage	$\pm 15\text{ V}$
Internal Power Dissipation	500 mW	Storage Temperature Range	-40°C to $+125^\circ\text{C}$
Differential Input Voltage	$\pm 30\text{ V}$	Operating Temperature Range	-20°C to $+75^\circ\text{C}$

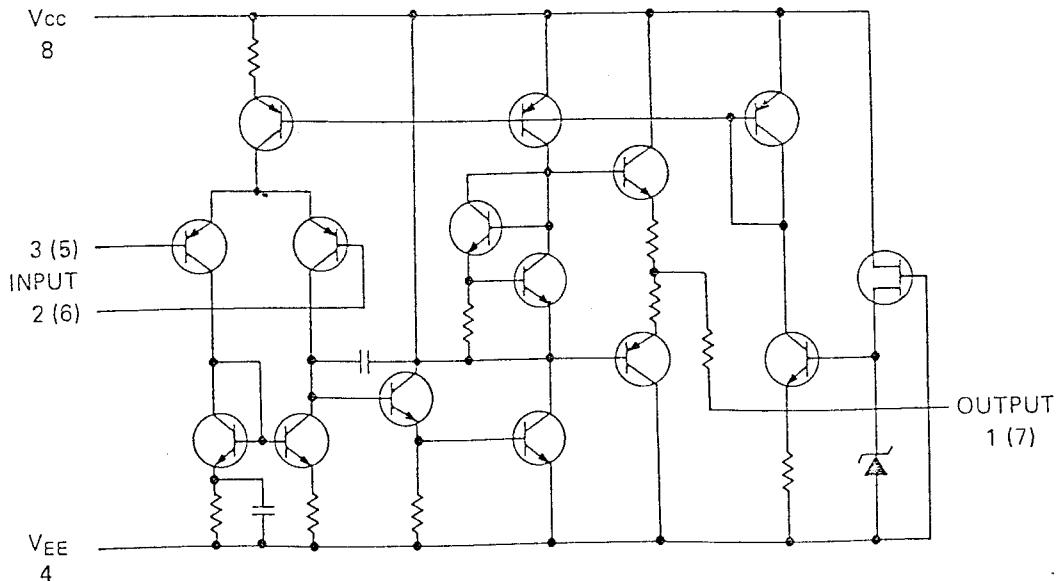
LECTRICAL CHARACTERISTICS (V_{CC} = $\pm 15\text{ V}$, T_A = $+25^\circ\text{C}$ unless otherwise noted.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
Input Offset Voltage	R _S $\leq 10\text{ k}\Omega$		0.5	6.0	mV
Input Offset Current			5	200	nA
Input Bias Current				500	nA
Large-Signal Voltage Gain	R _L $\geq 2\text{ k}\Omega$ V _{out} = $\pm 10\text{ V}$	86	100		dB
Output Voltage Swing	R _L $\geq 2\text{ k}\Omega$	± 10	± 13		V
Common Mode Rejection Ratio	R _S $\leq 10\text{ k}\Omega$	70	90		dB
Supply Voltage Rejection Ratio	R _S $\leq 10\text{ k}\Omega$		30	150	$\mu\text{V/V}$
Slew Rate	R _L $\geq 2\text{ k}\Omega$		1		V/ μs

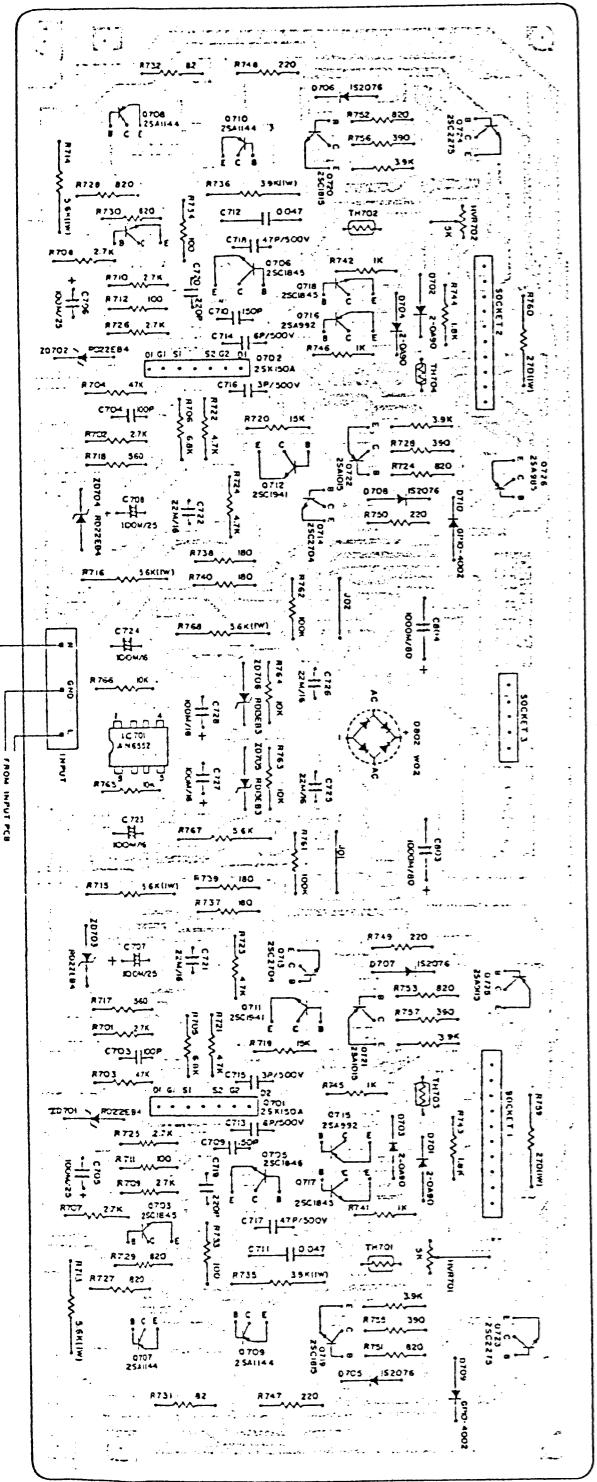
TERMINAL GUIDE (TOP VIEW)



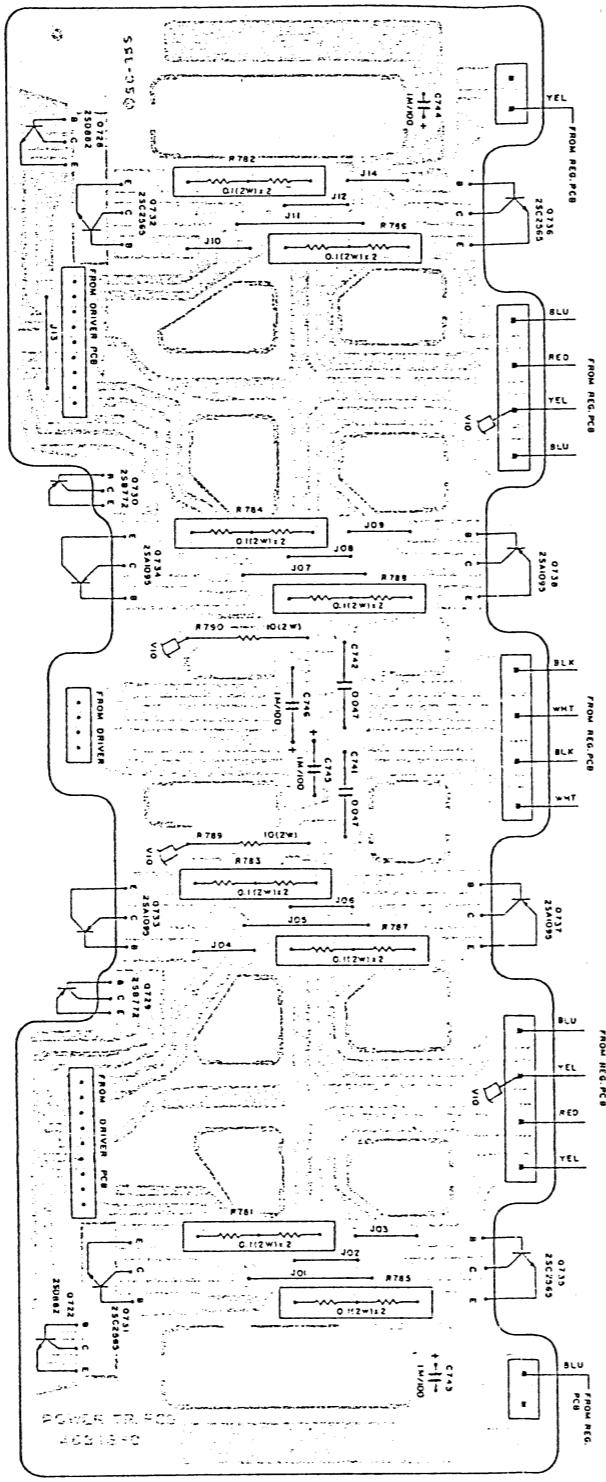
SCHEMATIC DIAGRAM (1/2 CIRCUIT)



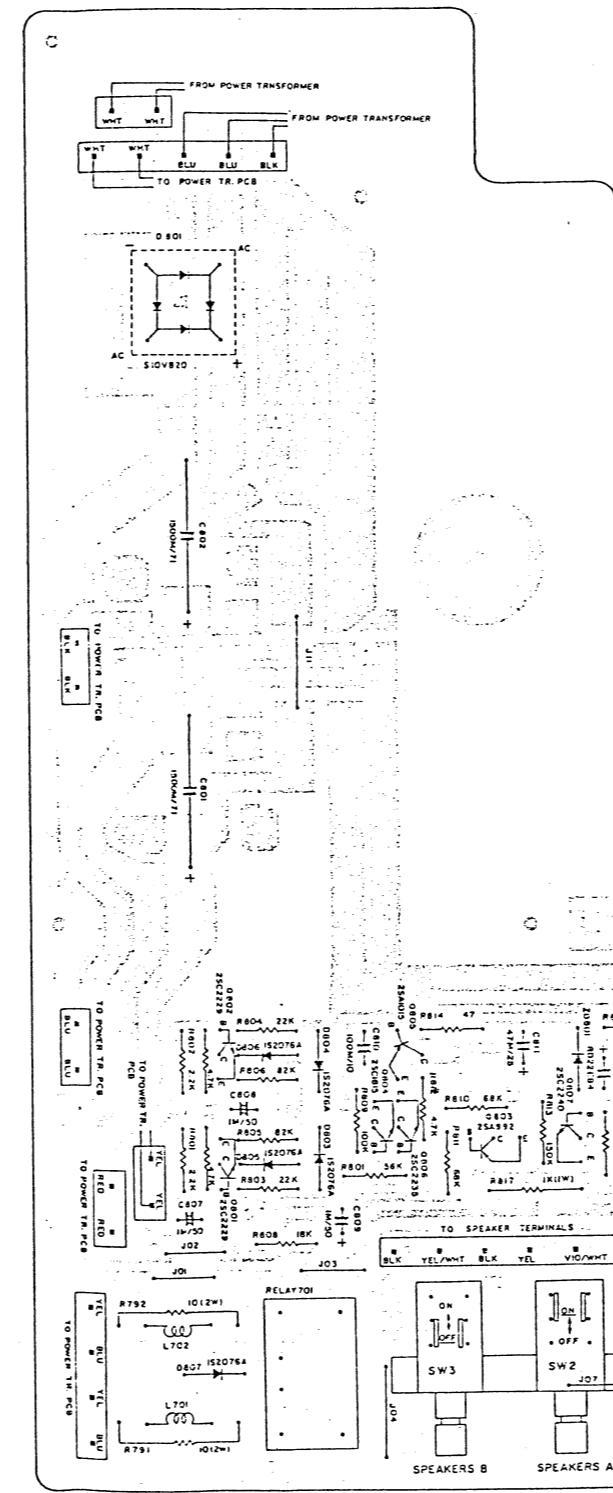
P.C. BOARD (BOTTOM VIEW) Figure 7



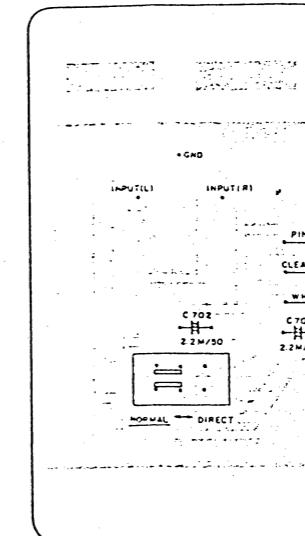
DRIVER PCB



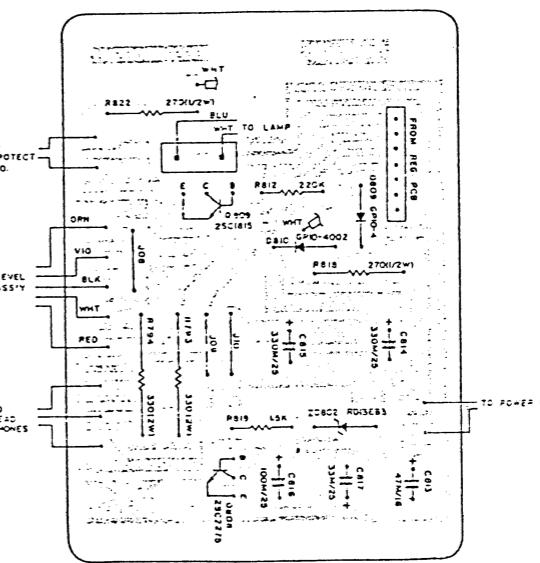
POWER TRANSISTORS PCB



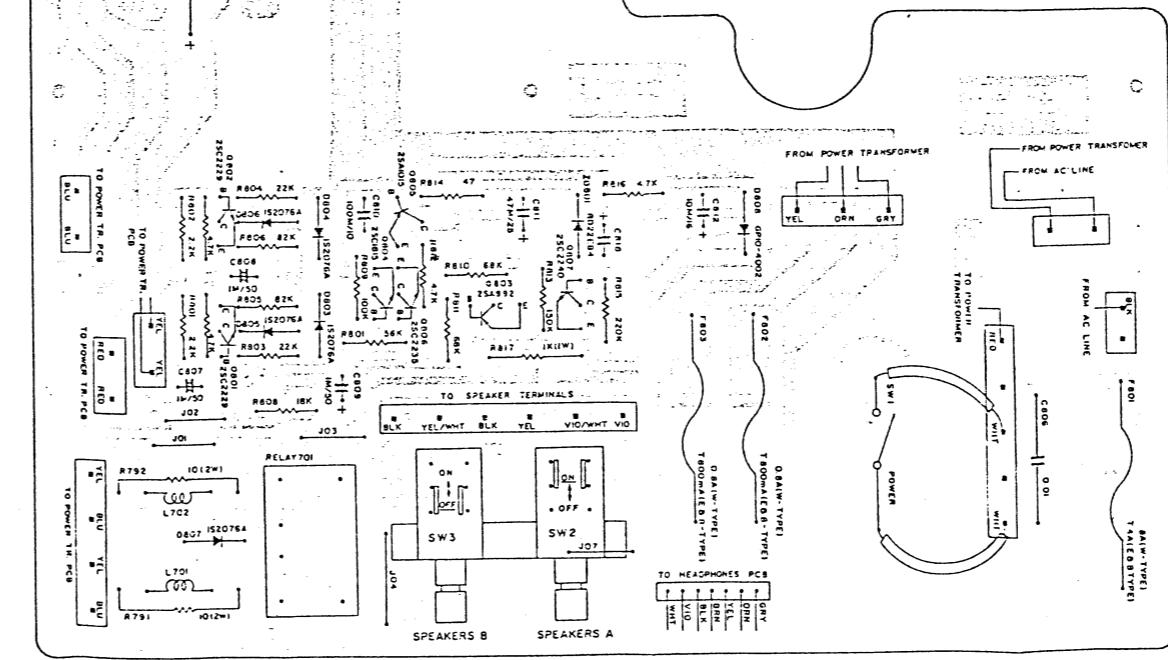
REGULATOR PCB



INPUT PCB



HEAD PHONES PCB



SCHEMATIC DIAGRAM

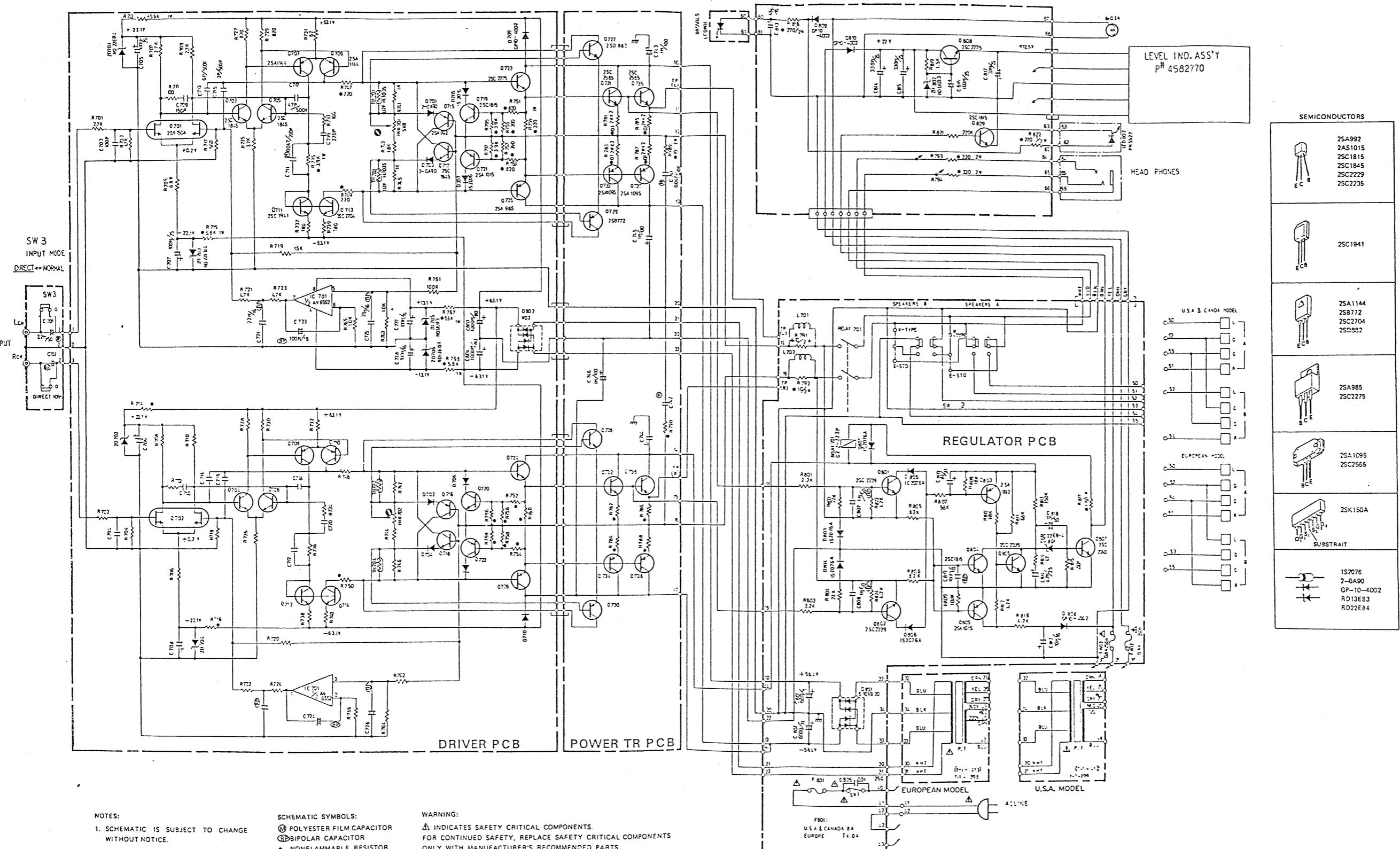


Figure 6